

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (mΩ)(TYP.)	I _D (A)	Q _g (TYP.)	
100	3.2at V _{GS} = 10 V	180	73.7 nC	
100	3.9at V _{GS} = 7.5 V	159	13.7110	



Top View N-Channel MOSFET

FEATURES

- Maximum 175 °C junction temperature
- \bullet 100 % R_{g} and UIS tested

RoHS

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- · Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS	$T_C = 25$ °C, unless othe	rwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20	v	
Continuous Dusis Courset /T. 150 °C)	T _C = 25 °C		180	
Continuous Drain Current (T _J = 150 °C)	T _C = 125 °C	I _D	90	
Pulsed Drain Current (t = 100 μs)		I _{DM}	700	Α
Avalanche Current	L = 0.1 mH	I _{AS}	50	
Single Avalanche Energy ^a	L = U.1 MH	E _{AS}	1238	mJ
Maximum Power Dissipation ^a	T _C = 25 °C		375 b	10/
	T _C = 125 °C	P _D	125 ^b	- w
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.75		

Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

Rev. A



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				<u>'</u>		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	-	4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μΑ
		$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	100	
		$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	2	mA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	180	-	-	Α
Drain-Source On-State Resistance ^a		$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	3.2	3.9	mΩ
	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 20 \text{ A}$	-	3.9	4.2	
Forward Transconductance a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	-	85	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	6730	-	pF
Output Capacitance	C _{oss}		-	671	-	
Reverse Transfer Capacitance	C _{rss}			95	-	
Total Gate Charge ^c	Qg		-	73.7	-	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	40.8	-	
Gate-Drain Charge ^c	Q _{gd}		-	12.6	-	
Gate Resistance	R _g	f = 1 MHz	-	1.25	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	13	-	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 1.67 Ω	-	22	-	ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 30$ A, $V_{GEN}=10$ V, $R_g=1$ Ω	-	27	-	
Fall Time ^c	t _f		-	9	-	
Drain-Source Body Diode Ratings a	nd Characteris	stics ^b (T _C = 25 °C)				
Pulsed Current (t = 100 µs)	I _{SM}		-	-	700	Α
Forward Voltage ^a	V _{SD}	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.86	1	V
Reverse Recovery Time	t _{rr}		-	88	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 30 A, di/dt = 100 A/μs	-	5	-	А
Reverse Recovery Charge	Q _{rr}		-	0.22	_	µС

Notes

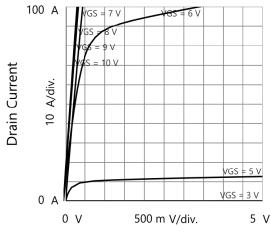
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

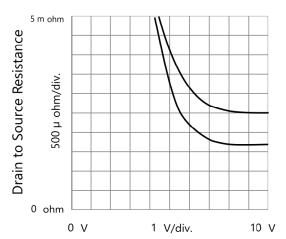
Rev. A



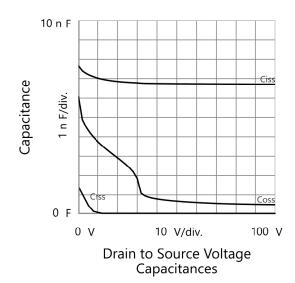
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

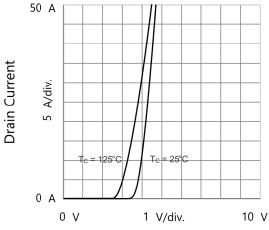


Drain to Source Voltage Output Characteristics

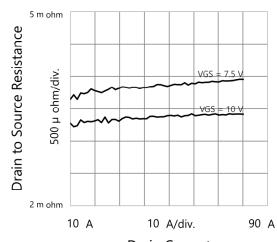


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

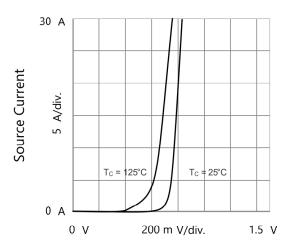




Gate to Source Voltage Transfer Characteristics



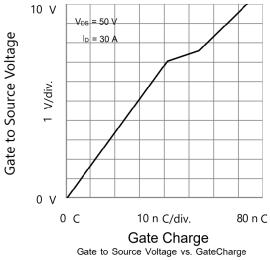
Drain Current
Drain to Source Resistance vs. Drain Current

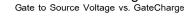


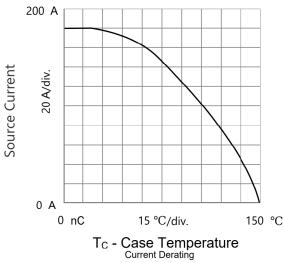
Source to Drain Voltage Body Diode Forward Characteristics

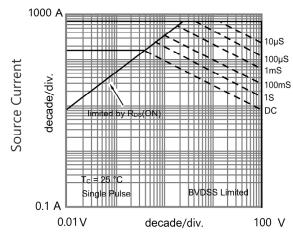


TYPICAL CHARACTERISTICS ($T_A = 25~^{\circ}C$, unless otherwise noted)

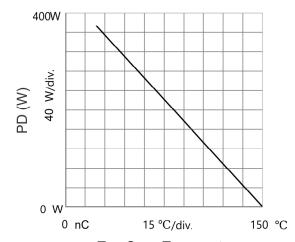








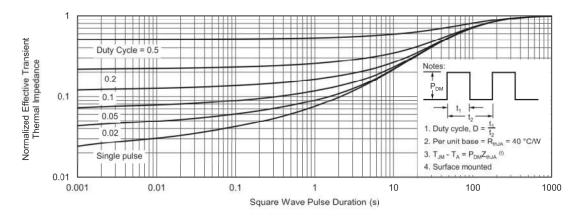
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature Power Derating



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)





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